

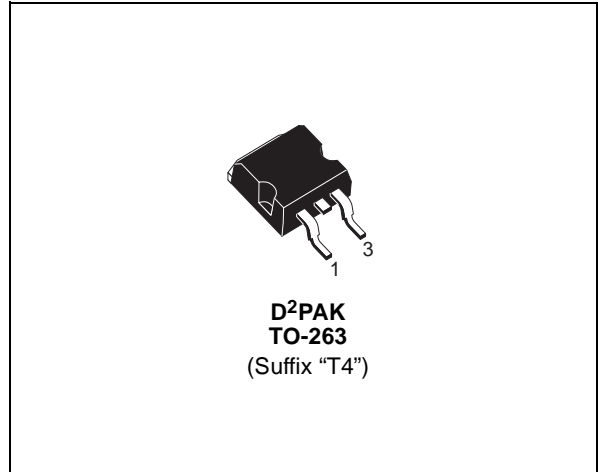


# STB60NE06L-16

## N-CHANNEL 60V - 0.014 Ω - 60A D<sup>2</sup>PAK STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB60NE06L-16	60 V	<0.016 Ω	60 A

- TYPICAL R<sub>DS(on)</sub> = 0.014 Ω
- AVALANCHE RUGGED TECHNOLOGY
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175 °C OPERATING TEMPERATURE
- LOW THRESHOLD DRIVE
- SURFACE-MOUNTING D<sup>2</sup>PAK (TO-263)  
POWER PACKAGE IN TUBE (NO SUFFIX) OR  
IN TAPE & REEL (SUFFIX "T4")



### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

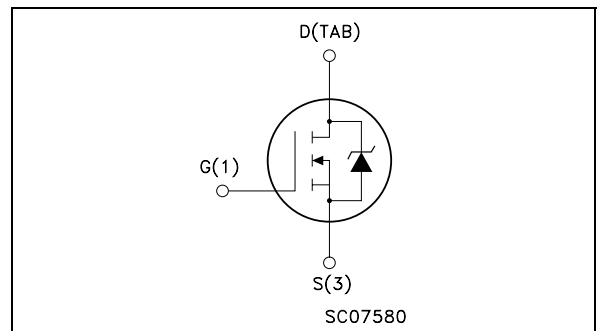
- HIGH CURRENT, HIGH SWITCHING SPEED
- SOLENOID AND RELAY DRIVERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate- source Voltage	± 15	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	60	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	42	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	240	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C	150	W
	Derating Factor	1	W/°C
dv/dt <sup>(1)</sup>	Peak Diode Recovery voltage slope	11	V/ns
E <sub>AS</sub> <sup>(2)</sup>	Single Pulse Avalanche Energy	400	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 175	°C
T <sub>j</sub>	Operating Junction Temperature		

(●) Pulse width limited by safe operating area.

### INTERNAL SCHEMATIC DIAGRAM



(1) I<sub>SD</sub> ≤ 60A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

(2) Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 60A, V<sub>DD</sub> = 35V

**STB60NE06L-16****THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case	Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 15V			±100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	1	1.6	2.5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 5 V I <sub>D</sub> = 30 A V <sub>GS</sub> = 10 V I <sub>D</sub> = 30 A		0.014 0.012	0.016 0.014	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 30 A		30		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V f = 1 MHz V <sub>GS</sub> = 0		4150		pF
C <sub>oss</sub>	Output Capacitance			590		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			150		pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 30\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		50 155		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 40\text{ V}$ $I_D = 60\text{ A}$ $V_{GS} = 5\text{ V}$		55 15 30	70	nC nC nC

**SWITCHING OFF**

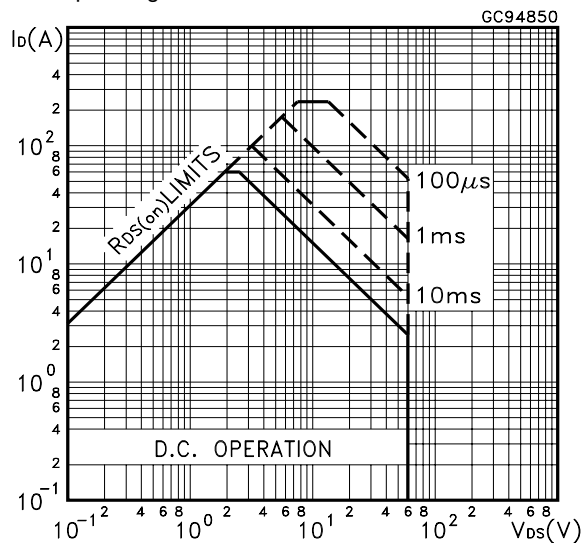
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$ $t_f$ $t_c$	Off-Voltage Rise Time Fall Time Cross-over Time	$V_{clamp} = 48\text{ V}$ $I_D = 20\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Inductive Load, Figure 5)		45 220 280		ns ns ns

**SOURCE DRAIN DIODE**

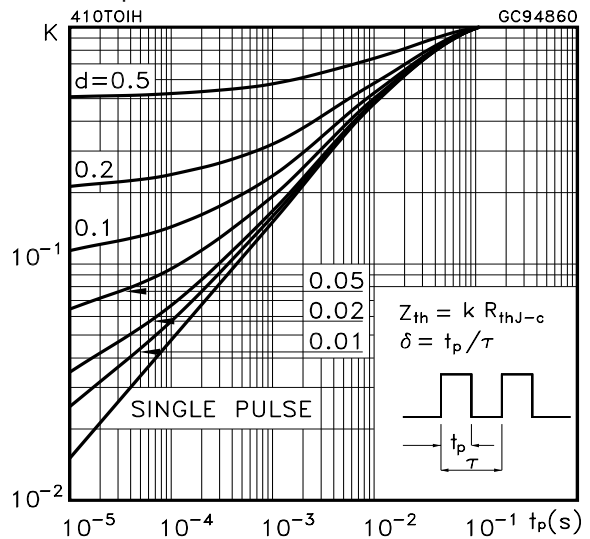
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(*)}$	Source-drain Current Source-drain Current (pulsed)				60 240	A A
$V_{SD}^{(*)}$	Forward On Voltage	$I_{SD} = 60\text{ A}$ $V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 60\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		85 300 7		ns nC A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
 (●) Pulse width limited by safe operating area.

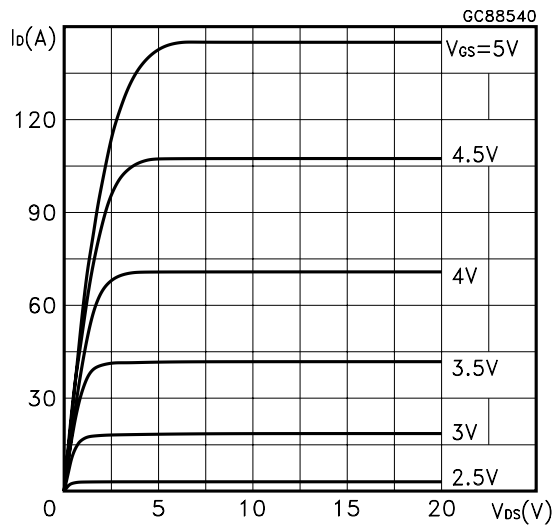
Safe Operating Area



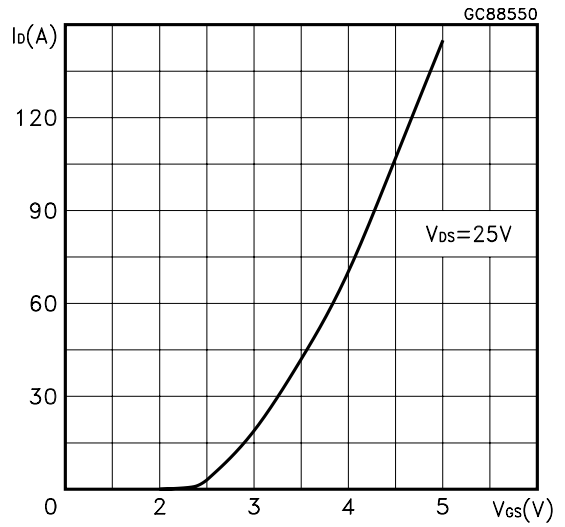
Thermal Impedance



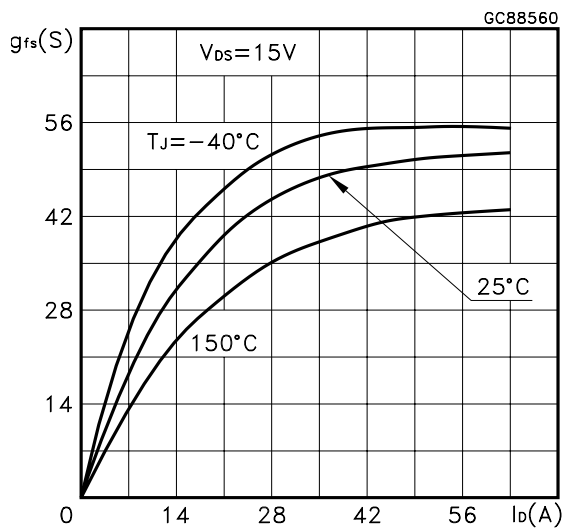
Output Characteristics



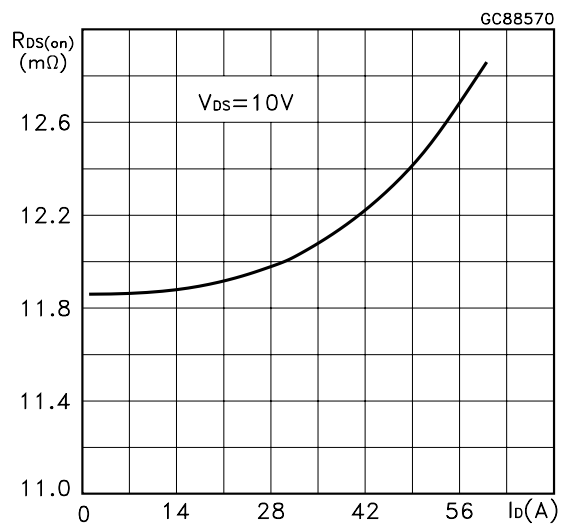
Transfer Characteristics



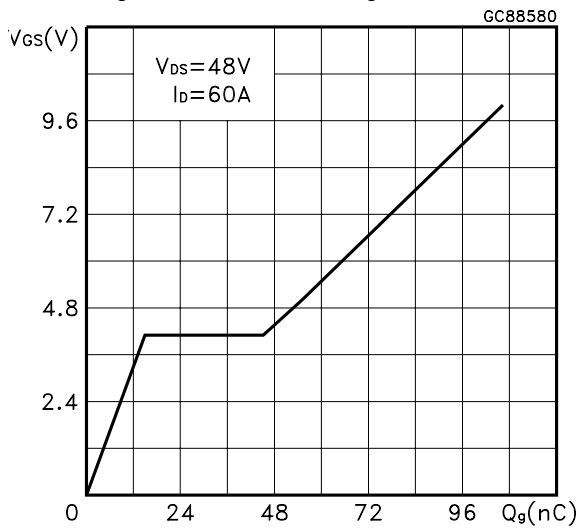
Transconductance



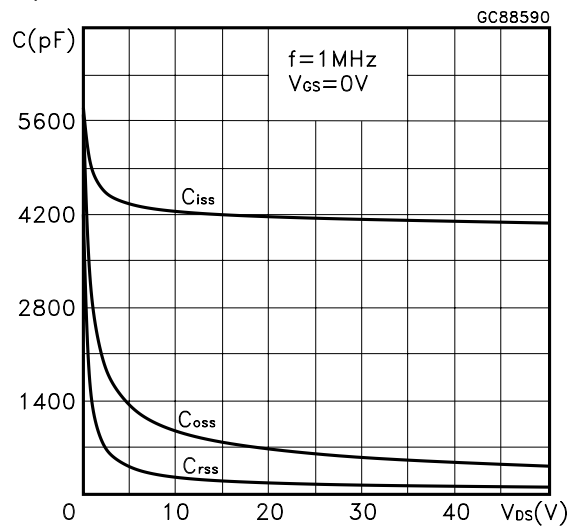
Static Drain-source On Resistance



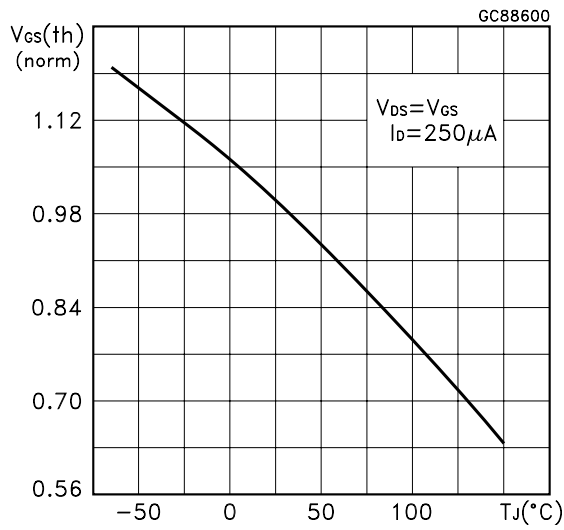
Gate Charge vs Gate-source Voltage



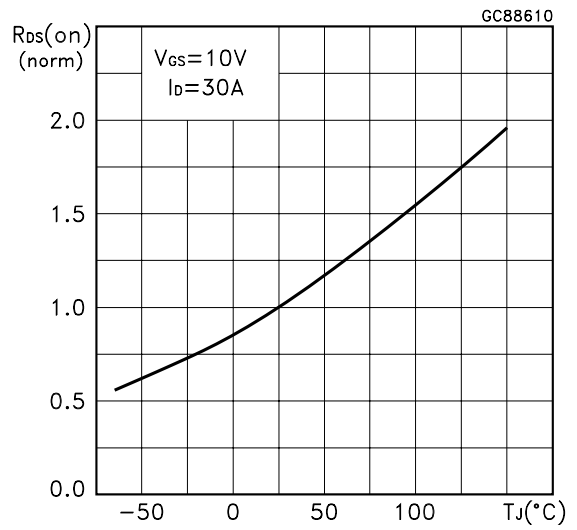
Capacitance Variations



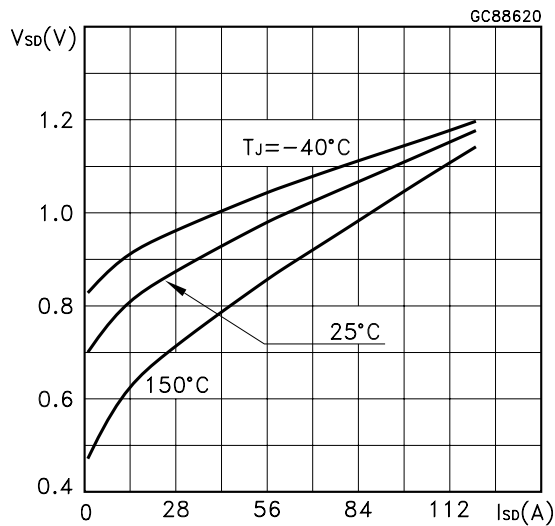
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage Temperature

Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load

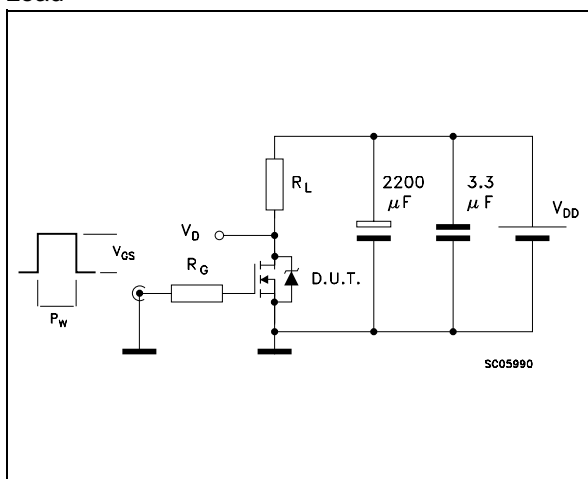


Fig. 4: Gate Charge test Circuit

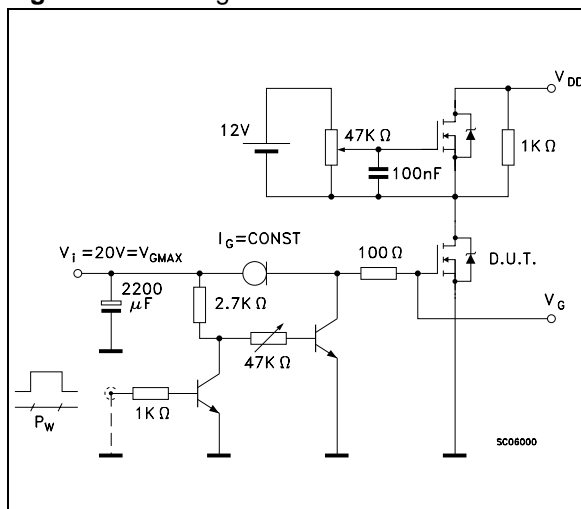
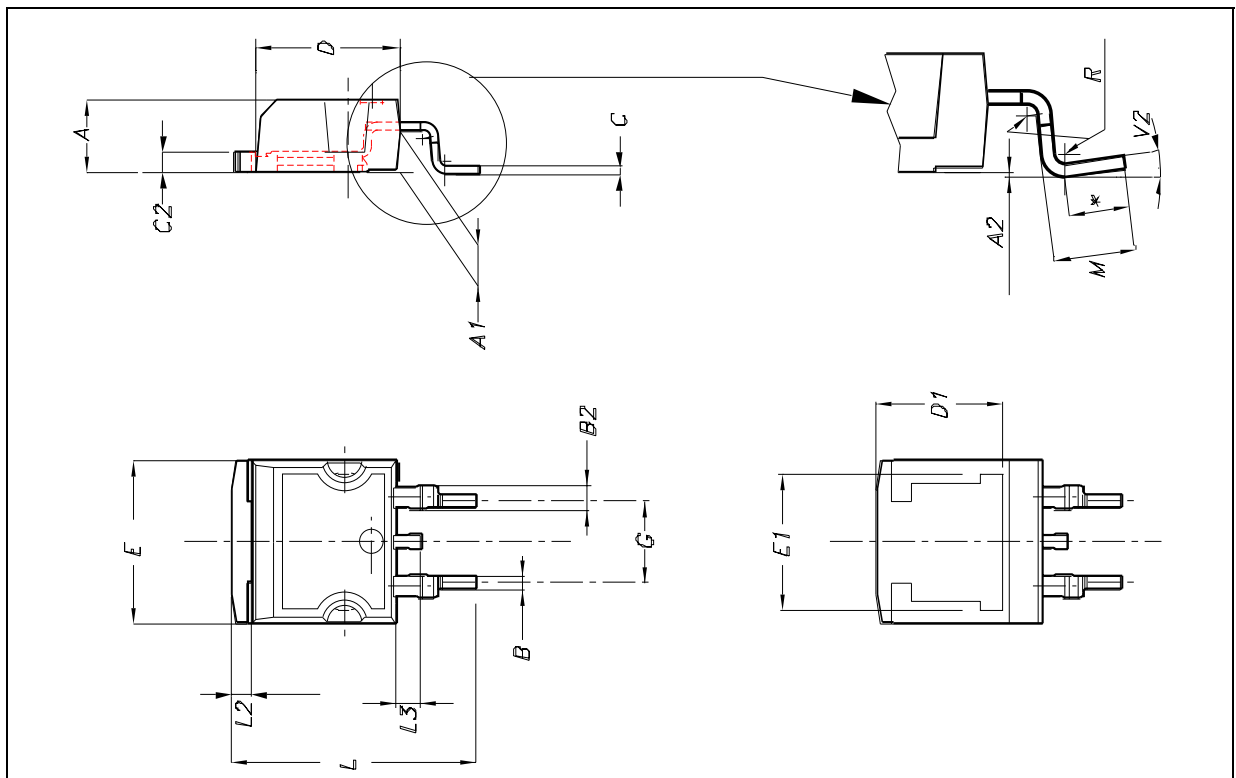


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



D<sup>2</sup>PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1	8.5				0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.016	
V2	0°		8°	0°		8°







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